



50A -1200V SiC Schottky Diode

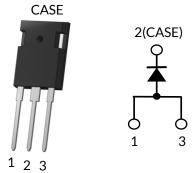
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DATASHEET

UJ3D1250K

Description

UnitedSiC offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Features

- Maximum operating temperature of 175°C
- Easy paralleling
- Extremely fast switching not dependent on temperature
- No reverse or forward recovery
- Enhanced surge current capability, MPS structure
- 100% UIS tested
- AEC-Q101 qualified

Typical applications

- Power converters
- Industrial motor drives
- Switch mode power supplies
- Power factor correction modules

Part Number	Package	Marking
UJ3D1250K	TO-247-3L	UJ3D1250K







Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units	
DC blocking voltage	V _R		1200	V	
Repetitive peak reverse voltage, T _J =25°C	V _{RRM}		1200	V	
Surge peak reverse voltage	V _{RSM}		1200	V	
Maximum DC forward current	I _F	T _C = 112°C	50	А	
Non-repetitive forward surge current sine halfwave	I _{FSM}	T_{C} = 25°C, t_{p} = 10ms	275	А	
Repetitive forward surge current		T _C = 25°C, t _p = 10ms	163.5	А	
sine halfwave, D=0.1	I _{FRM}	$T_{\rm C}$ = 110°C, $t_{\rm p}$ = 10ms	99.6		
Non-repetitive peak forward current	I _{F,max} –	T _C = 25°C, t _p = 10μs	2400	^	
		T_{C} = 110°C, t_{p} = 10µs	2400	A	
i ² t value	∫i ² dt	T _C = 25°C, t _p = 10ms	378	A ² s	
Power dissipation	D	T _c = 25°C 319		14/	
	P _{tot} –	T _C = 112°C	134	W	
Maximum junction temperature	T _{J,max}		175	°C	
Operating and storage temperature	T _J , T _{STG}		-55 to 175	°C	
Soldering temperatures, wavesoldering only allowed at leads	T _{sold}	1.6mm from case for 10s	260	°C	

Thermal Characteristics

Parameter	Symbol	Test Conditions	Value			Units
			Min	Тур	Max	Units
Thermal resistance, junction-to-case	$R_{ ext{ hetaJC}}$			0.36	0.47	°C/W



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Electrical Characteristics (T_J = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			L los tes
			Min	Тур	Max	- Units
Forward voltage	V _F	I _F = 50A, T _J =25°C	-	1.5	1.7	V
		I _F = 50A, T _J =150°C	-	1.95	2.4	
		I _F = 50A, T _J =175°C	-	2.2	2.7	
Reverse current	I _R	V _R =1200V, T _J =25°C	-	52	400	μΑ
		V _R =1200V, T _J =175°C	-	900		
Total capacitive charge ⁽¹⁾	Q _c	V _R =800V		240		nC
Total capacitance	С	V_R =1V, f = 1MHz		2340		pF
		V _R =400V, f = 1MHz		224		
		V _R =800V, f = 1MHz		198		
Capacitance stored energy	E _C	V _R =800V		72		μJ

(1) Q_c is independent on T_J , di_F/dt , and I_F as shown in the application note USCi_AN0011.

Typical Performance Diagrams

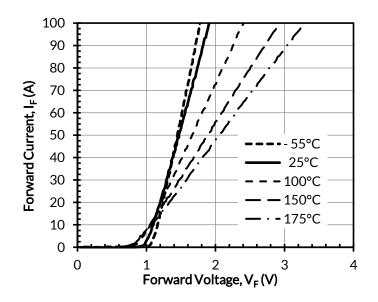


Figure 1. Typical forward characteristics

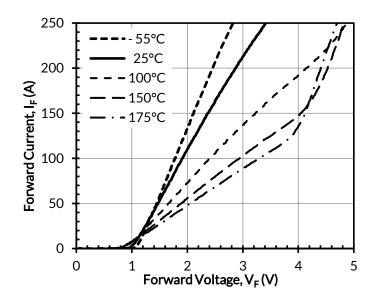


Figure 2. Typical forward characteristics in surge current



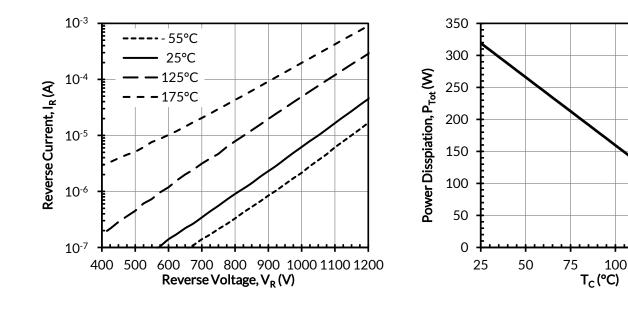


Figure 3. Typical reverse characteristics

Figure 4. Power dissipation

Related Devices

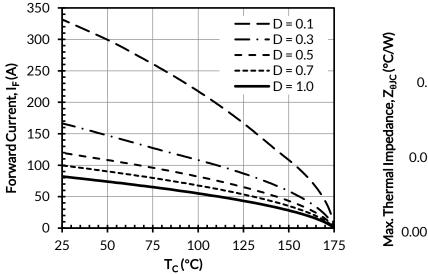
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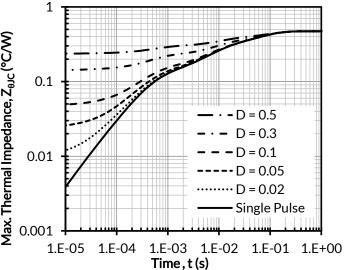


Figure 5. Diode forward current

Figure 6. Maximum transient thermal impedance





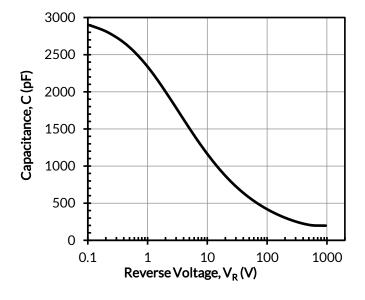


Figure 7. Capacitance vs. reverse voltage at 1MHz

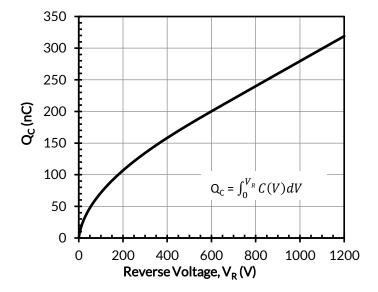


Figure 8. Typical capacitive charge vs. reverse voltage

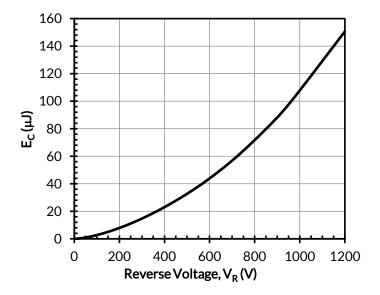


Figure 9. Typical capacitance stored energy vs. reverse voltage









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